

In re Appln. of KUNITSUGU et al.
Application No. Unassigned

ABSTRACT AMENDMENTS

Replace the Abstract with:

A semiconductor laser device includes a dielectric multilayer film with a reflectance of 40% or more, ~~formed~~ on at least one of optical exit faces of a laser chip, ~~wherein the~~. The dielectric multilayer film includes a ~~dielectric~~ film of tantalum oxide (Ta_2O_5) and another ~~dielectric~~ film of a dielectric oxide, such as aluminum oxide (Al_2O_3), and silicon oxide (SiO_2), ~~the~~. The tantalum oxide film ~~having~~ has an optical absorption coefficient smaller than that of silicon (Si) ~~film~~ and thermal stability in emission superior to that of titanium oxide (TiO_2) ~~film~~, thereby remarkably improving the ~~COD~~ catastrophic optical damage degradation level of the laser chip.